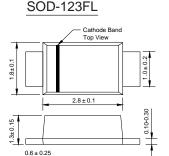


DSR1A THRU DSR1M

SUFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere



Dimensions in millimeters

 3.7 ± 0.2

FEATURES

- Glass passivated device
- Ideal for surface mouted applications
- Low reverse leakage
- Metallurgically bonded construction
- ◆ High temperature soldering guaranteed: 250°C/10 seconds,0.375"(9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip

Terminals : Solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

Mounting Position : Any

Weight :0.006 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

6.1.g.0 p.1.400 1.4.1 1.4.7 0.5.1 1.2,1 0.5.1 0.1 1.4.1 0.1 1.5.4 0.4.1 0.1 1.5.4 0.4.1 0.1 1.5.4 0.4.1 0.1 1.5									
	SYMBOLS	DSR1A	DSR1B	DSR1D	DSR1G	DSR1J	DSR1K	DSR1M	UNITS
MDD Catalog Number		S1A	S1B	S1D	S1G	S1J	S1K	S1M	00
Maximum repetitive peak reverse voltage	VRRM	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current	l(AV)	1.0							Amp
at Ta=65°C (NOTE 1)	I(AV)								
Peak forward surge current									
8.3ms single half sine-wave superimposed on	IFSM 25.0							Amps	
rated load (JEDEC Method) TL=25°C									
Maximum instantaneous forward voltage at 1.0A	VF	1.1							Volts
Maximum DC reverse current Ta=25℃		10.0 50.0							μА
at rated DC blocking voltage Ta=125℃	l _R								
Typical junction capacitance (NOTE 2)	Cì	4							pF
Typical thermal resistance (NOTE 3)	RθJA	180							K/W
Operating junction and storage temperature range	ТЈ,Тѕтс	-55 to +150							°C

Note: 1. Averaged over any 20ms period.

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

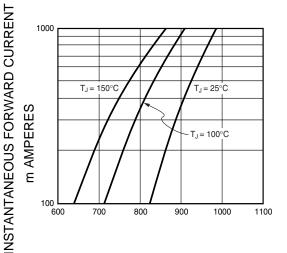
3. Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length, P.C.B. mounted

RATINGS AND CHARACTERISTIC CURVES DSR1A THRU DSR1M

CAPACITANCE, pF

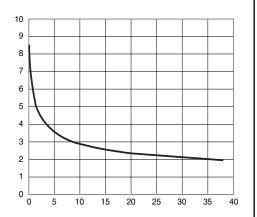
AVERAGE FORWARD CURRENT,

FIG.1 -TYPICAL FORWARD CHARACTERISTIC



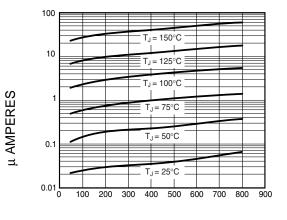
INSTANTANEOUS FORWARD VOLTAGE, mV

FIG.2 - TYPICAL JUNCTION CAPACITANCE



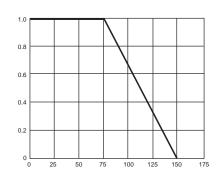
REVERSE VOLTAGE, VOLTS

FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS



INSTANTANEOUS REVERSE VOLTAGE, V

FIG.4 - FORWARD DERATING CURVE



AMBIENT TEMPERATURE, °C

INSTANTANEOUS REVERSE CURRENT

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